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View Online at https://aerobasegroup.com/nsn/5961-01-067-1075

#### Inclosure Material:

Metal

**Overall Length:** 

1.125 inches

Mounting Facility Quantity:

1

#### Internal Configuration:

Junction contact

#### **Mounting Method:**

Threaded stud

#### **Features Provided:**

Hermetically sealed case

#### **Overall Width Across Flats:**

Between 1.031 inches and 1.062 inches

#### Thread Size:

0.250 inches

#### Semiconductor Material:

Silicon

#### Voltage Rating In Volts Per Characteristic:

560.0 reverse voltage, peak

#### Current Rating Per Characteristic:

50.00 amperes forward current, total rms megahertz

#### Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank

#### Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

#### **Special Features:**

Junction pattern arrangement: pnpn

#### **Test Data Document:**

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

#### **Thread Series Designator:**

Unf

## Terminal Type And Quantity:

1 threaded stud and 2 tab, solder lug

## **Specification Data:**

81349-mil-s-19500/280 government specification

### Shelf Life:

N/a

- Unit Of Measure:
- --
- Demilitarization:
- No

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